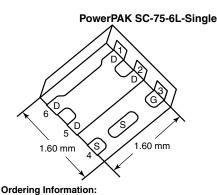


Vishay Siliconix

P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY								
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)					
- 20	0.035 at V _{GS} = - 4.5 V	- 9 ^a						
	0.049 at V _{GS} = - 2.5 V	_S = - 2.5 V _ 9 ^a						
- 20	0.079 at V _{GS} = - 1.8 V		13 nC					
	0.157 at V _{GS} = - 1.5 V	- 2						



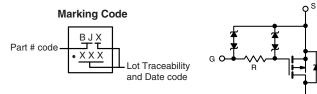
SiB457EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
- Low On-Resistance
- 100 % R_g Tested
- Typical ESD Performance: 2500 V
- Built in ESD Protection with Zener Diode
- Compliant to RoHS Directive 2011/65/EU

APPLICATIONS

- Load Switch for Portable Devices
- Load Switch for Charging Circuits





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
Parameter		Symbol	Limit	Unit				
Drain-Source Voltage		V _{DS}	- 20	V				
Gate-Source Voltage		V _{GS}	± 8	v				
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 \text{ °C}$ $T_{C} = 70 \text{ °C}$ $T_{A} = 25 \text{ °C}$ $T_{A} = 70 \text{ °C}$	- ال	- 9 ^a - 9 ^a - 6.8 ^{b, c} - 5.5 ^{b, c}	A				
Pulsed Drain Current		I _{DM}	- 25					
Continuous Source-Drain Diode Current	$T_{C} = 25 \text{ °C}$ $T_{A} = 25 \text{ °C}$	۱ _s	- 9 ^a - 2 ^{b, c}					
Maximum Power Dissipation	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	P _D -	13 8.4 2.4 ^{b, c} 1.6 ^{b, c}	W				
Operating Junction and Storage Temperature Range Soldering Recommendations (Peak Temperature) ^{d, 6}		T _J , T _{stg}	- 55 to 150 260	°C				

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient ^{b, f} $t \le 5 s$		R _{thJA}	41	51	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	7.5	9.5	0/11				

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 105 °C/W.



FREE

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static		· · · · · · · · · · · · · · · · · · ·		•		•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$	- 20			V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 12		mV/°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η = - 230 μΑ		2.5				
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.4		- 1	V		
Cata Sauraa Laakaga	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 5	μΑ		
Gate-Source Leakage		$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$			± 0.5			
Zara Cata Valtaga Drain Current		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1			
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS}{\leq}$ - 5 V, V_{GS} = - 4.5 V	- 15			A		
		V _{GS} = - 4.5 V, I _D = - 4.8 A		0.029	0.035			
	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, \text{ I}_{\text{D}} = -4 \text{ A}$ 0.040						
Drain-Source On-State Resistance ^a		V _{GS} = - 1.8 V, I _D = - 3.3 A		0.060	0.079	Ω		
		V _{GS} = - 1.5 V, I _D = - 1.5 A		0.085	0.157			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 4.8 A		16		S		
Dynamic ^b		· · · · · · · · · · · · · · · · · · ·		•				
Total Gate Charge	0	$V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_{D} = -6.8 \text{ A}$		22	44			
Cata Caura Ohanna	Q _g			13	26	nC		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 6.8 A		1.2				
Gate-Drain Charge	Q _{gd}			3				
Gate Resistance	Rg	f = 1 MHz	0.28	1.4	2.8	kΩ		
Turn-On Delay Time	t _{d(on)}			0.34	0.51			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1.8 Ω		0.90	1.35			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 5.5 A, V_GEN = - 4.5 V, R_g = 1 Ω		3	4.5			
Fall Time	t _f			1.90	2.90			
Turn-On Delay Time	t _{d(on)}			0.17	0.26	μs		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1.8 Ω		0.45	0.70	-		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 5.5 A, V_GEN = - 8 V, R_g = 1 Ω		5.5	8.30			
Fall Time	t _f			2	3.5	1		
Drain-Source Body Diode Characteristi	cs	·			·	·		
Continuous Source-Drain Diode Current	ا _S	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$			- 9	A		
Pulse Diode Forward Current	I _{SM}				- 25			
Body Diode Voltage	V _{SD}	I _S = - 5.5 A, V _{GS} = 0 V		- 0.85	- 1.2	V		

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

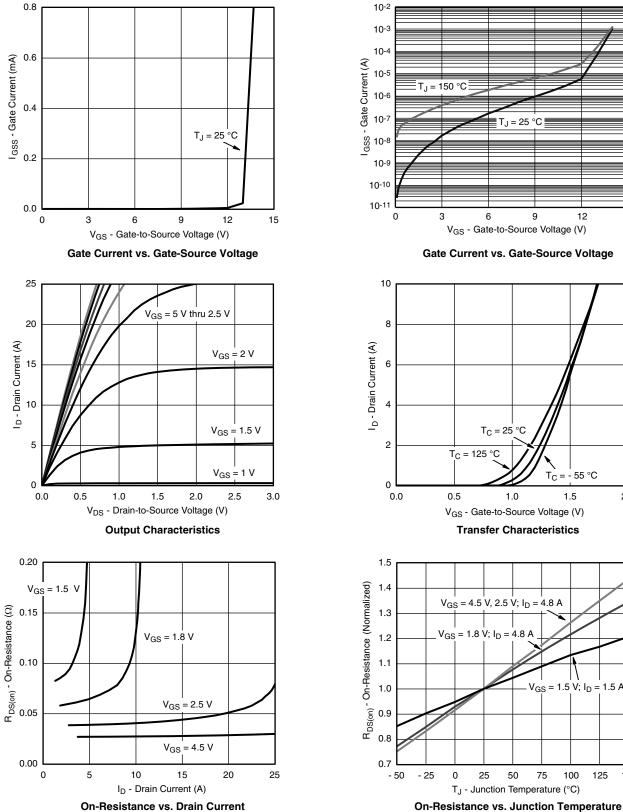


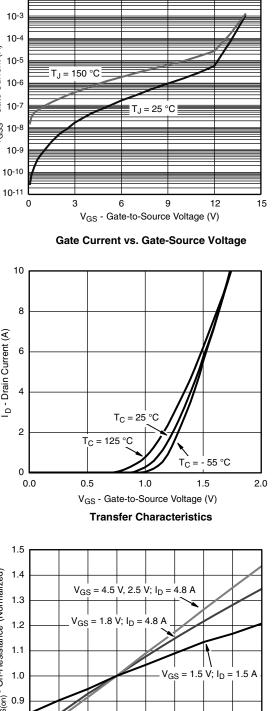
Document Number: 64816

S12-0497-Rev. C, 05-Mar-12

SiB457EDK Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





For more information please contact: pmostechsupport@vishay.com www.vishay.com

0

25

50

T_J - Junction Temperature (°C)

75

100

125

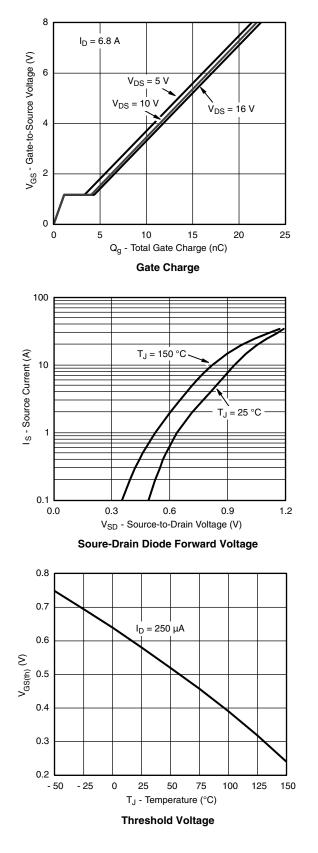
150

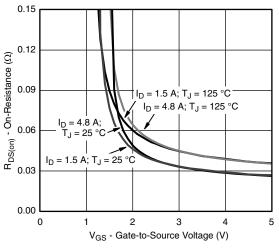
3

Vishay Siliconix

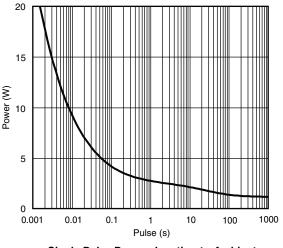


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

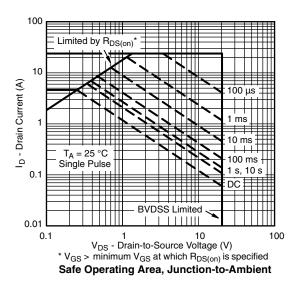




On-Resistance vs. Gate-to-Source Voltage







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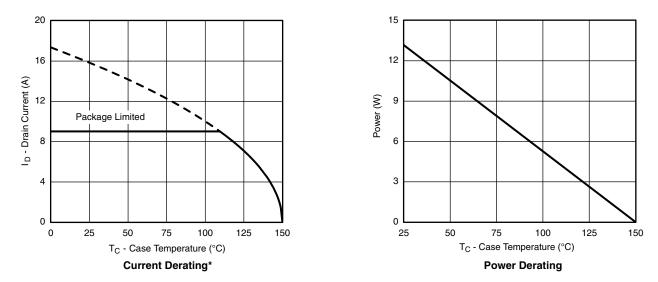
Document Number: 64816 S12-0497-Rev. C, 05-Mar-12

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Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

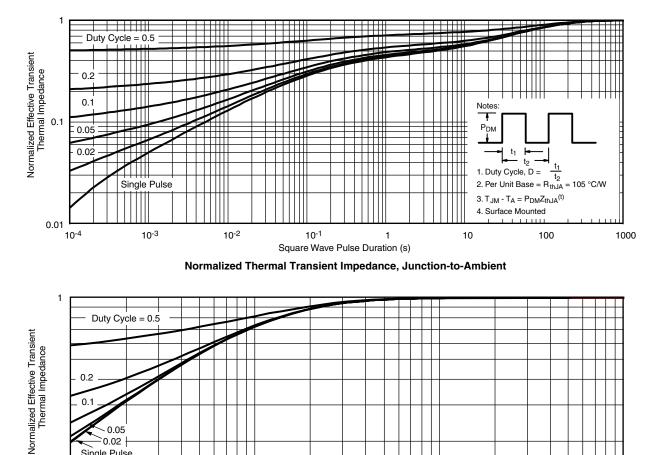


Vishay Siliconix

- 0.05 [≥]0.02 Single Pulse

0.1 10-4

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



10⁻³

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?64816.

Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

10-2

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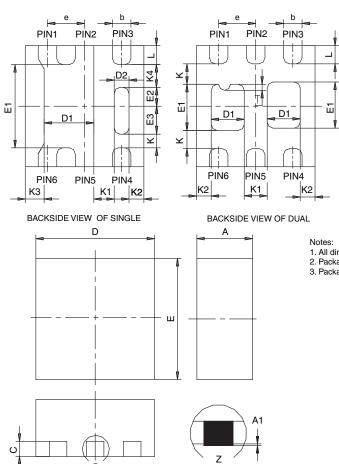
10-1

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Package Information

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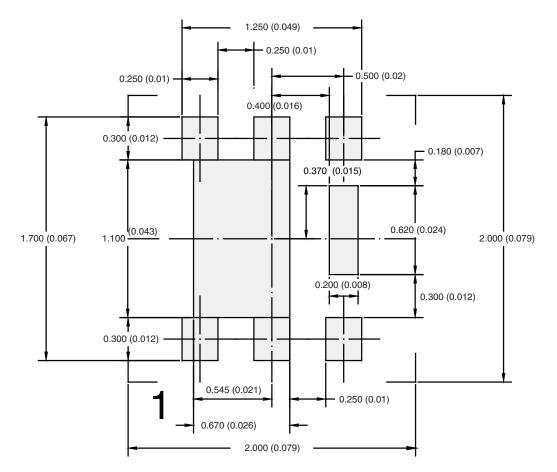
- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DETAIL Z

		SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е		0.50 BSC			0.020 BSC		0.50 BSC			0.020 BSC			
К		0.180 TYP 0.007 TYP				0.245 TYP			0.010 TYP				
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP			
K2	0.200 TYP 0.008 TYP			0.200 BSC 0.008 T				0.008 TYP					
K3	0.255 TYP 0.010 TYP												
K4	0.300 TYP			0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
Т							0.03	0.08	0.13	0.001	0.003	0.005	
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935													



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC75-6L Single



Dimensions in mm/(Inches)

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